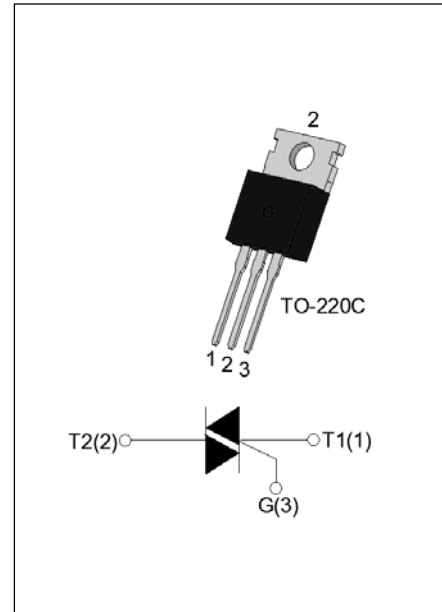


**JST16C-800B 16A TRIAC**

Rev.A.1.0

**DESCRIPTION:**

The JST16C-800B triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. From T2 terminals to external heatsink. Package TO-220C is RoHS compliant.


**MAIN FEATURES**

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
$V_{DRM}/V_{RRM}$	800	V
$I_{GT\ I/II/III/IV}$	50/50/50/70	mA

**ABSOLUTE MAXIMUM RATINGS**

Parameter		Symbol	Value	Unit
Storage junction temperature range		$T_{stg}$	-40-150	°C
Operating junction temperature range		$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )		$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )		$V_{RRM}$	800	V
RMS on-state current ( $T_c \leq 100^\circ\text{C}$ )		$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )		$I_{TSM}$	160	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )			176	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )		$I^2t$	128	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ , $f=100\text{Hz}$ , $T_j=125^\circ\text{C}$ )	I - II	$di/dt$	100	$\text{A}/\mu\text{s}$
	III-IV		50	
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )		$I_{GM}$	4	A
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )		$P_{G(AV)}$	0.5	W
Peak gate power		$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25^\circ\text{C}$ ; non-repetitive, off-state; FIG.7)		$V_{pp}$	1	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12\text{V}$ $R_L=33\Omega$	I - II - III	MAX.	50	mA
		IV		70	
$V_{GT}$		ALL	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=3.3\text{K}\Omega$	ALL	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I - III - IV	MAX.	70	mA
		II		100	
$I_H$	$I_T=500\text{mA}$		MAX.	60	mA
dV/dt	$V_D=540\text{V}$ Gate Open $T_j=125^\circ\text{C}$		MIN.	1000	V/ $\mu\text{s}$
(dV/dt) <sub>c</sub>	(dI/dt) <sub>c</sub> =7A/ms, $T_j=125^\circ\text{C}$		MIN.	12	V/ $\mu\text{s}$
$t_{on}$	$I_G=80\text{mA}$ $I_A=400\text{mA}$ $I_R=40\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	5	$\mu\text{s}$
$t_{off}$				50	

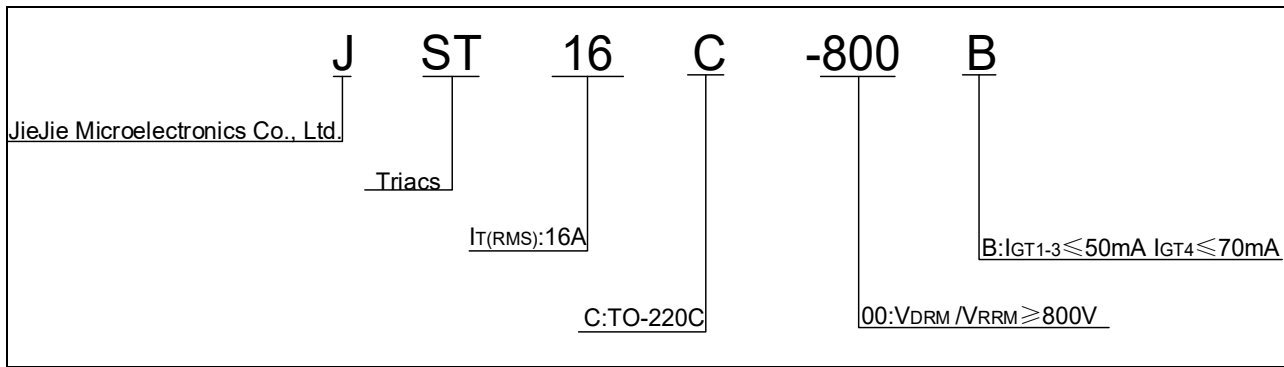
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=22.5\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=125^\circ\text{C}$	0.77	V
$R_D$	Dynamic resistance	$T_j=125^\circ\text{C}$	30	m $\Omega$
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	0.5	mA

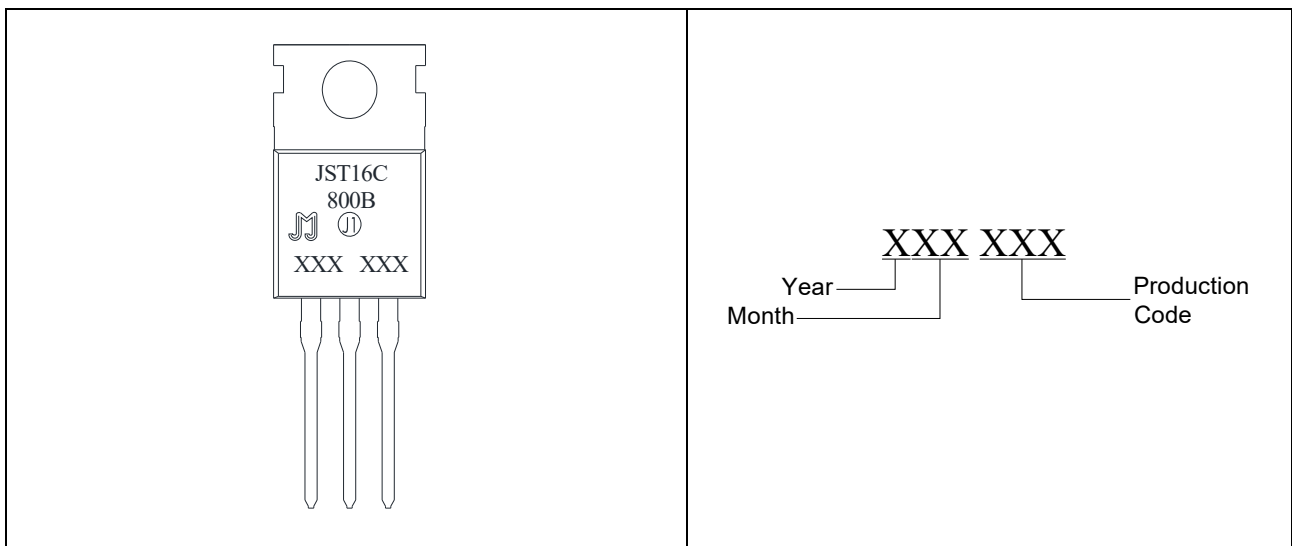
**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.1	$^\circ\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^\circ\text{C}/\text{W}$

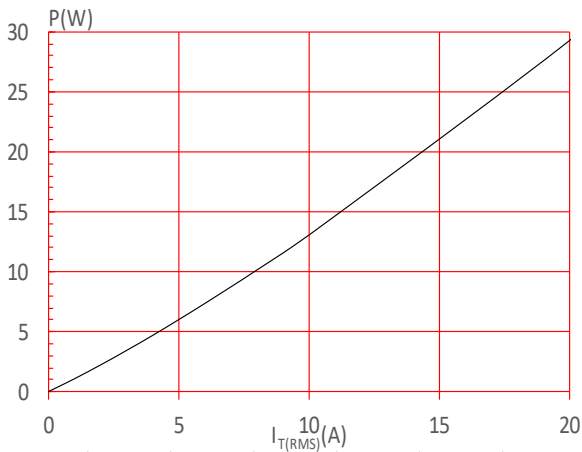
**ORDERING INFORMATION**



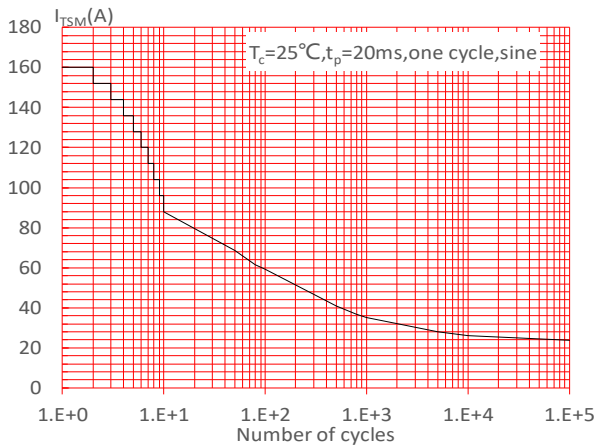
**MARKING**



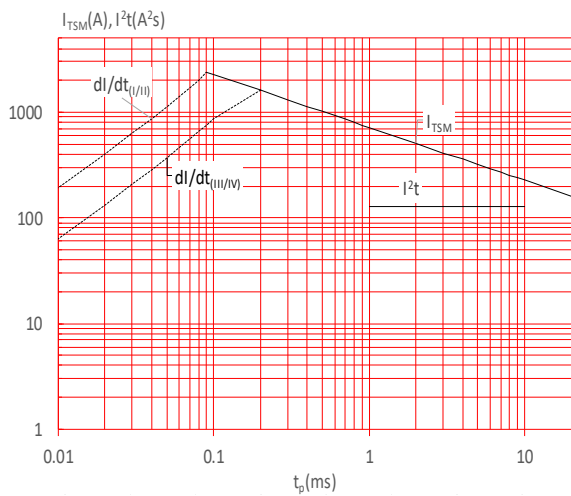
**FIG.1** Maximum power dissipation versus RMS on-state current



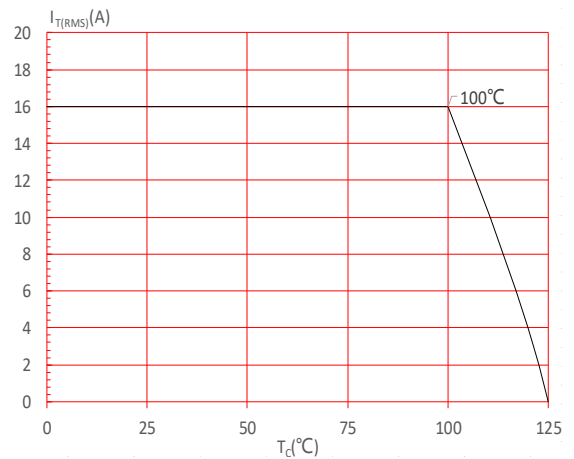
**FIG.3:** Surge peak on-state current versus number of cycles



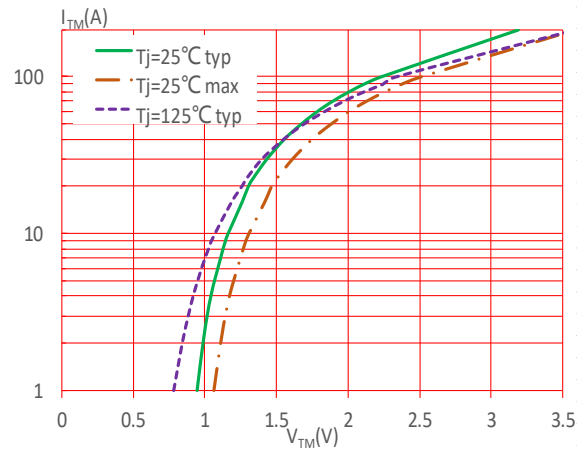
**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( I - II :  $di/dt < 100\text{A}/\mu\text{s}$ ; III-IV :  $di/dt < 50\text{A}/\mu\text{s}$ )



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** On-state characteristics



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature

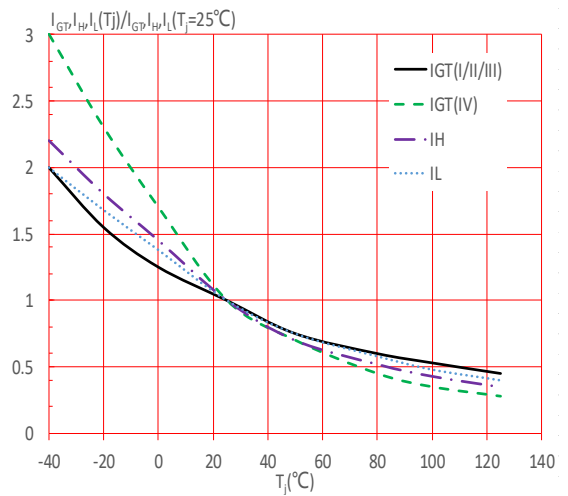
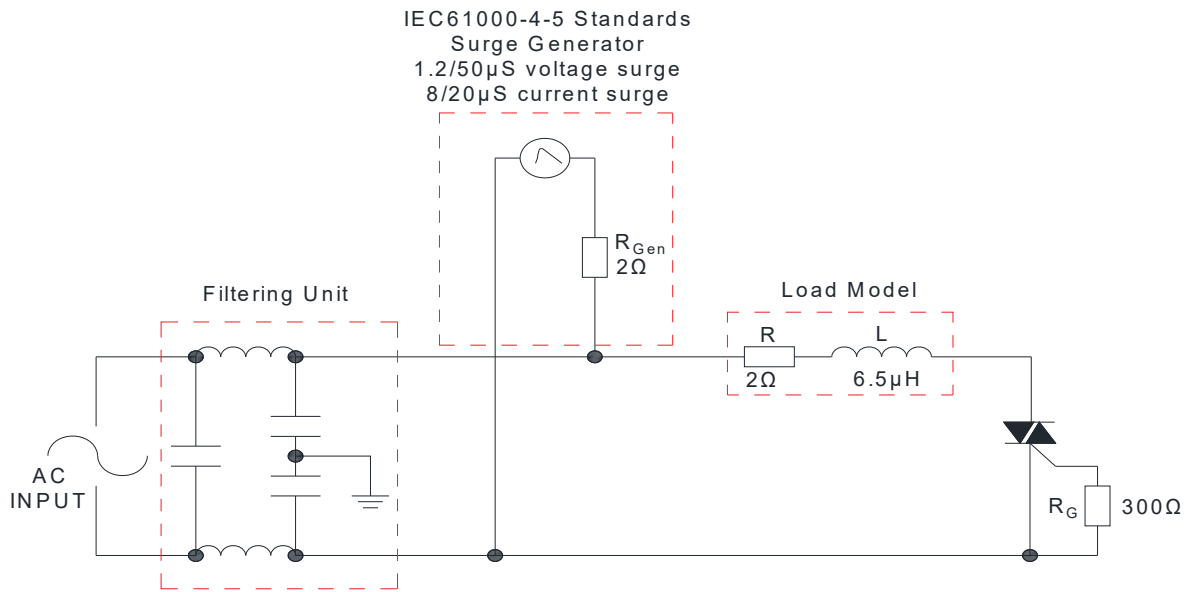


FIG.7: Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



## SHAPING AND SOLDERING PARAMETERS

Refer to 《Instructions for installation of plastic-sealed in-line power devices》 released by JieJie.

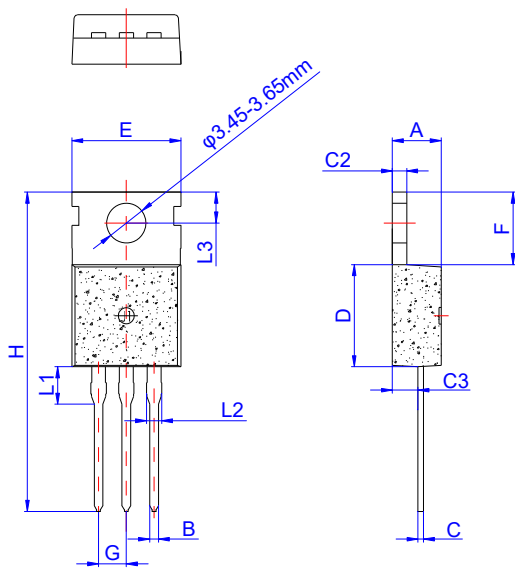
**ORDERING INFORMATION**

Order code	Voltage V <sub>DRM</sub> /V <sub>RPM</sub> (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I -II-III	IV			
JST16C-800B	800	50	70	TO-220C	50	Tube

**Document Revision History**

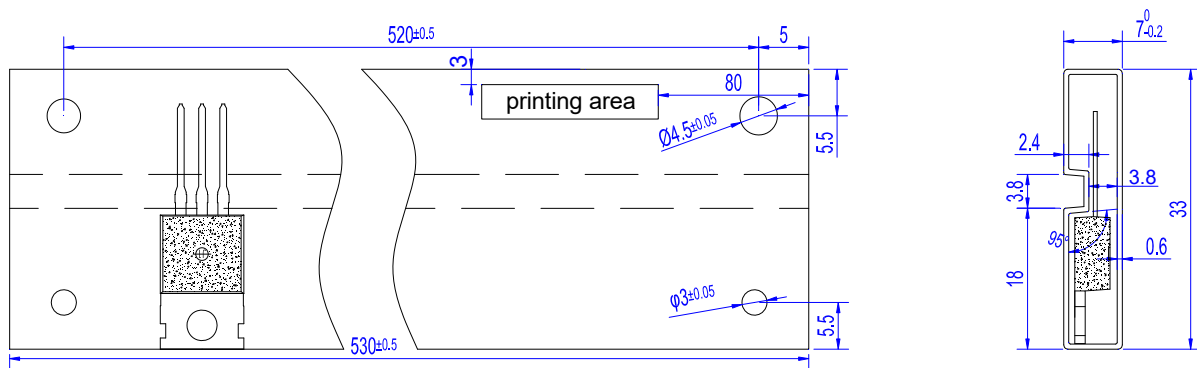
Date	Revision	Changes
Apr.14, 2023	A.1.0	Last updated

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.70		0.90	0.028		0.035
C	0.45		0.60	0.018		0.024
C2	1.25		1.35	0.049		0.053
C3	2.20		2.60	0.087		0.102
D	8.90		9.90	0.350		0.390
E	9.90		10.3	0.390		0.406
F	6.30		6.90	0.248		0.272
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1	2.70		3.30	0.106		0.130
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116

DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220C	TUBE	50	1,000	5,000

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